ABSTRACT OF THE DISCLOSURE

A plasma etching method and apparatus in which a processing gas is supplied from a shower plate arranged on an electrode opposed to an electrode for generating a plasma or a sample toward the sample center, and the gas is transformed into a plasma thereby to etch the sample. RF power is applied between a sample stage and the electrode to apply the energy to charged particles in the plasma to thereby etch the sample. In the process, apart from the incidence of the charged particles to the sample, the charged particles enter also the shower plate of the electrode by application of the RF power. The charged particles entering the processing gas supply holes of the shower plate are neutralized to prevent abnormal discharge on the shower plate and consequently suppress the generation of foreign matter.